Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A process for generating a structured ~~layer~~ component, comprising:

forming ~~at least one~~ a first layer on a substrate,

forming a second layer on the first layer,

generating on the ~~at least one~~ second layer a mask with a first structure and second structure,

performing an isotropic process on the ~~at least one~~second layer, which transfers the first structure into the second layer, and

after performing the isotropic process, performing an anisotropic process on the ~~at least one~~ first layer, which transfers the second structure into the first layer, wherein the first structure is different from the second structure.

2. (Canceled)

3. (Previously Presented) The process of claim 1, wherein the first structure of the mask is a rough structure and the second structure of the mask is a fine structure, and the smallest expansion of the rough structure is at least twice as large as the smallest expansion of the fine structure.

4. (Currently Amended) The process of claim [[2]]1, wherein performing an isotropic process includes using an etching agent which is selective for the second layer.

5. (Currently Amended) The process of claim [[2]]1, wherein forming at least one of the first layer or the second layer includes forming a metal layer.

6. (Currently Amended) The process of claim [[2]]1, wherein the first layer is a Pt layer and the second layer is an Au layer.

7. (Currently Amended) The process of claim 1, wherein generating on the ~~at least one~~ second layer a mask includes forming a photoresist layer and performing photolithography on the photoresist layer to form the mask.

8. (Currently Amended) The process of claim [[2]]1, wherein:

performing the isotropic process removes the second layer below the mask, and

the mask structure is lowered onto the first layer in areas in which the second layer beneath the mask is removed.

9. (Currently Amended) The process of claim [[2]]1:

performing an isotropic process includes structuring the second layer with wet chemical isotropic etching, and

performing an anisotropic process includes structuring the first layer with a dry anisotropic etching process.

10. (Currently Amended) The process of claim [[2]]1, wherein performing an isotropic process on the second layer removes the second layer entirely except for one or several areas below the mask.

11. (Previously Presented) The process of claim 1, wherein after performing the anisotropic process, the mask is removed.

12. (Currently Amended) The process of claim [[2]]1, wherein:

the first layer is formed on functional layers on the substrate,

the first layer and second ~~layers~~ layer are metal layers,

the first structure of the mask is a geometrically ~~formed~~ shaped area and the second structure is a linear structure that originates from the first structure,

performing the isotropic process structures the second layer into an area which lies below the geometrically ~~formed~~ shaped area of the mask and forms a bond pad,

performing the anisotropic process transfers the linear ~~structures~~ structure of the mask into the first layer, forming a contact ~~lines~~ line, and

the bond pad has approximately a shape of the ~~mask~~ first structure and a cross section which widens towards the substrate.

13. (Previously Presented) The process of claim 12, wherein there are multiple linear structures and the linear structures of the mask are in grate arrangements.

14. (Currently Amended) An electrical component, comprising:

a substrate, and

a first layer and a second layer on the substrate, wherein the first layer is different from the second layer, the second layer is structured into ~~at least~~ a first structure ~~and a second structure~~, the first layer is structured into a second structure and the first layer is between the second layer and the substrate; ~~arranged on the substrate~~,

wherein the first structure in the second layer is structured by an isotropic structuring process, ~~and~~ the second structure is structured by an anisotropic structuring process and the first structure is different from the second structure, and ~~the first structure and the second structure are structured from at least one layer~~

wherein the first layer and the second layer form electrical conductors of the electrical component.

15. (Canceled)

16. (Currently Amended) The electrical component of claim [[15]]14, wherein the first structure includes a bond pad and the second structure includes contact lines.

17. (Previously Presented) The electrical component of claim 16, formed as a surface wave component, wherein:

the contact lines are electrically conducting microstructures, and

the substrate includes a piezoelectric crystal.

18. (Previously Presented) The electrical component of claim 16, wherein the contact lines are formed in a grate pattern.

19. (Currently Amended) The electrical component of claim 16, wherein:

the contact lines include a first electrically conducting ~~material~~metal, and

the bond pad includes [[a]]the first electrically conducting ~~layer~~ metal and a second electrically conducting metal~~layer, wherein the first layer includes a first electrically conducting material, and the second layer includes a second electrically conducting material and the first layer is different from the second layer~~.

20. (Currently Amended) The electrical component of claim 19, wherein the first electrically conducting ~~material~~ metal is Pt and the second electrically conducting ~~material~~ metal is Au.

21. (Previously Presented) The electrical component of claim 14, wherein the substrate additionally includes active layers.

22. (Previously Presented) The electrical component of claim 21, wherein the component is an LED in which the active layers include p- and n- endowed semiconductor layers.

23. (Canceled)

24. (Currently Amended) The process of claim [[23]]1 wherein

performing the isotropic process only transfers the first structure into the second ~~at least one~~ layer, and

performing the anisotropic process ~~only~~ transfers the second structure into the ~~at least one~~ first layer.

25. (Currently Amended) An electrical component, comprising:

a substrate having a main surface with a first structure and second structure arranged thereon,

wherein the first structure possesses a cross section which widens towards the substrate and in a direction perpendicular to the main surface of the substrate has a geometric form ~~whose circumference possesses additional~~ with a perimeter that has recessed areas deviating from the geometric form.

26. (Previously Presented) The electrical component of claim 25, wherein the first structure is a rough structure and the second structure is a fine structure, and the smallest extension of the rough structure is at least twice as large as the smallest extension of the fine structure.

27. (Previously Presented) The electrical component of claim 25, wherein the first structure consists of a bond pad, and the second structure of contact lines.

28. (New) The process of claim 1, wherein forming the second layer includes forming the second layer of a material that is different that material of the first layer.

29. (New) The process of claim 1, wherein performing the anisotropic process transfers the first structure into the first layer.

30. (New) The component of claim 14, wherein the first layer includes the first structure.